

Silicon PNP Power Transistors

2SB1292

DESCRIPTION

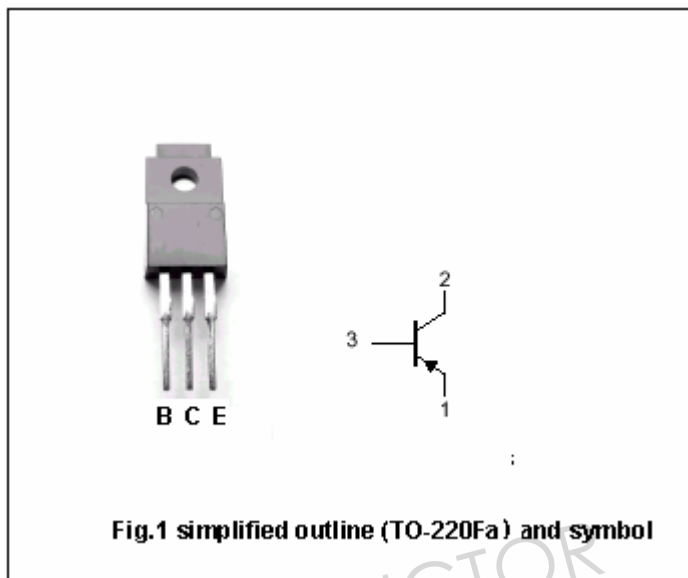
- With TO-220Fa package
- Low saturation voltage
- Complement to type 2SD1832
- Excellent DC current gain characteristics
- Wide area of safe operation

APPLICATIONS

- For use in low frequency power amplifier applications, power drivers and DC-DC converters

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Emitter |
| 2 | Collector |
| 3 | Base |



Absolute maximum ratings(Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| V_{CBO} | Collector-base voltage | Open emitter | -60 | V |
| V_{CEO} | Collector-emitter voltage | Open base | -60 | V |
| V_{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I_C | Collector current (DC) | | -5 | A |
| I_{CM} | Collector current-Peak | | -10 | A |
| P_C | Collector power dissipation | $T_C=25$ | 30 | W |
| | | $T_a=25$ | 2 | |
| T_j | Junction temperature | | 150 | |
| T_{stg} | Storage temperature | | -55~150 | |

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CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-1mA, I _B =0 | -60 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =-50 μA, I _E =0 | -60 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =-50 μA, I _C =0 | -5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-3A; I _B =-0.3A | | | -1.5 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =-3A; I _B =-0.3A | | | -1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-60V; I _E =0 | | | -10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =-4V; I _C =0 | | | -10 | μA |
| h _{FE} | DC current gain | I _C =-1A; V _{CE} =-5V | 100 | | 320 | |
| f _T | Transition frequency | I _C =-0.5A; V _{CE} =-5V | | 12 | | MHz |
| C _{ob} | Output capacitance | I _E =0; V _{CB} =-10V, f=1MHz | | 150 | | pF |

◆ h_{FE} Classifications

| E | F |
|---------|---------|
| 100-200 | 160-320 |

PACKAGE OUTLINE

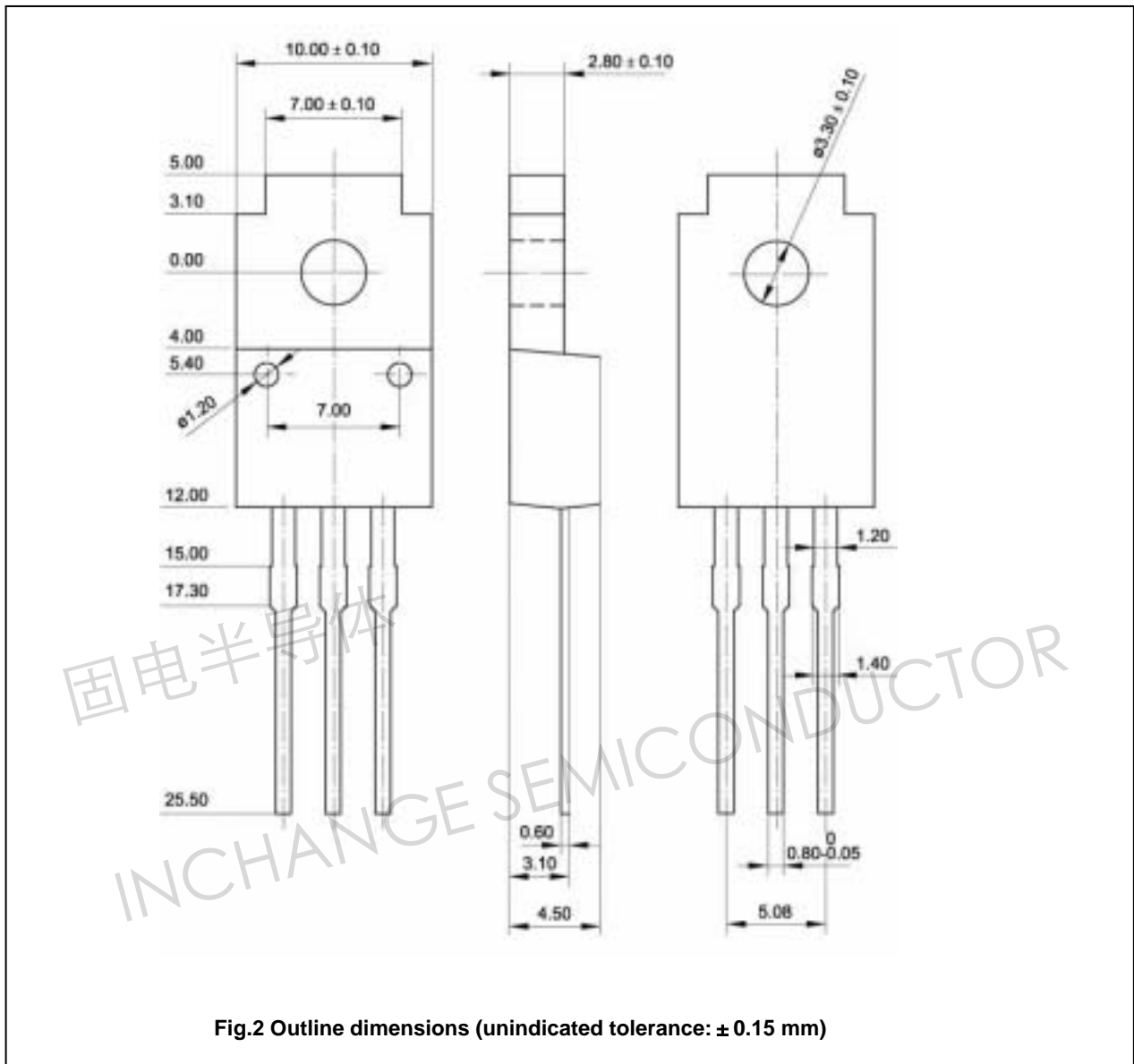


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)